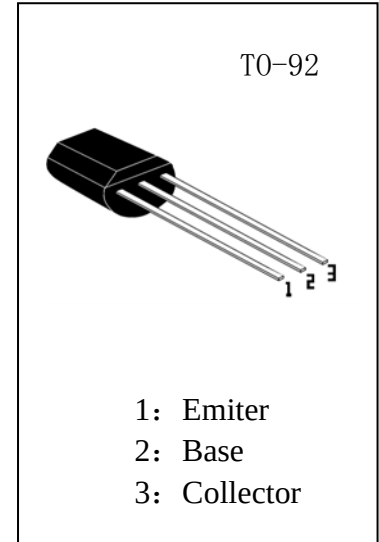


AMPLIFIER TRANSISTOR

- $V_{ce0}=160V$
- 高耗散功率 $P_c=625mW$
- 与 2N5401 对管

极限参数(Absolute Maximum Ratings) $T_a=25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	180	V
Collector-Emitter Voltage	V_{ceo}	160	V
Emitter-Base Voltage	V_{ebo}	6	V
Collector Current	I_c	600	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$


电性能(Electrical Characteristic) $T_a=25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=100\mu A$ $I_e=0$	180			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=1mA$ $I_b=0$	160			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=10\mu A$ $I_c=0$	6			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=120V$, $I_e=0$			50	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=4V$, $I_c=0$			50	nA
I_{ceo}	Collector Cutoff Current	$V_{ce}=160V$, $I_b=0$			1	μA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c=10mA$, $I_b=1mA$		0.05	0.15	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c=50mA$, $I_b=5mA$		0.08	0.20	V
$V_{be(sat)1}$	Base-Emitter Saturation Voltage	$I_c=10mA$, $I_b=1mA$		0.75	0.9	V
$V_{be(sat)2}$	Base-Emitter Saturation Voltage	$I_c=50mA$, $I_b=5mA$		0.85	1.0	V
H_{fe1}	DC Current Gain	$V_{ce}=5V$, $I_c=1mA$	80			
H_{fe2}	DC Current Gain	$V_{ce}=5V$, $I_c=10mA$	80		300	
H_{fe3}	DC Current Gain	$V_{ce}=5V$, $I_c=50mA$	30			
C_{ob}	Output Capacitance	$V_{cb}=10V$, $I_e=0$, $f=1MHz$			6	PF
f_T	Current Gain-Bandwidth product	$V_{ce}=10V$, $I_c=10mA$,	100		300	MHz
NF	Noise Figure	$I_c=250\mu A$, $V_{ce}=5V$ $f=10Hz\sim 15.7kHz$, $R_s=1k\Omega$			8	dB

CLASS	B	C	D	E
Hfe2	80-100	100-150	150-200	200-300